Hetero –SiC '09 International workshop on 3C-SiC hetero-epitaxy May 6th-7th, 2009 – Catania, Italy http://hetero.imm.cnr.it

Introduction

The third International Workshop Hetero-SiC'09 is a follow-up of the first European Workshop on SiC hetero-epitaxy (HeT-SiC 2005) held in Krippen (Germany) from April 26th to May 1st 2005 and of the second edition held in Grenoble (France) on June 28-29th 2007.

Aim of the workshop is to have a dedicated forum on SiC heteroepitaxy to effort all the specific subjects related both to the possibility to grow SiC on other materials and to grow epitaxially different SiC polytypes to take advantage of the bandgap engineering.

Hetero-SiC'09 will be organized in Catania jointly with the third "International Workshop on Advanced semiconductor Materials and devices for Power Electronics applications" – WASMPE'09, allowing to broad the subjects exploring device fabrication and industrial applications. The goal is to allow young and advanced researchers from different fields to meet together for a single-session workshop of invited and contributed presentations taking advantage of the *MANSiC* European RTN project framework.

For a better impact when reviewing the important issues, only a limited number of high standard presentations will be accepted.

Scientific committee

Giuseppe Abbondanza (ETC/LPE, Italy)
Gabriel Ferro (University of Lyon, France)
Kestutis Jarasiunas (University of Vilnius, Lithuania)
Rositza Yakimova (University of Linköping, Sweden)
Michael Krieger (University of Erlangen, Germany)
Gerhard Pensl (University of Erlangen, Germany)
Stephen Saddow (University of South Florida, USA)
Marcin Zielinski (Novasic, France)

Important dates

Abstract Submission:

March 20th 2009

Notification of acceptance:

April 1st 2009

Manuscript Submission:

April 20th 2009







Local Chairs

Vito Raineri (CNR-IMM, Catania, Italy) Fabrizio Roccaforte (CNR-IMM, Catania, Italy)



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